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| <b>INFORMATION<br/>DISCLOSURE<br/>CITATION<br/>PTO-1449</b> | Atty. Docket No. 990852A                          | Divisional of S.N. 09/361,246       |
|   | Applicant(s): Nobuhiko HAYASHI, et al. 09/955 600 |                                     |
|   | Filing Date: Herewith 9/19/01                     | Group Art Unit: To Be Assigned 2813 |

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| Examiner<br>Initial | Document<br>No. | Name | Date | Class | Subclass | Filing Date<br>(If appropriate) |
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| AA<br>AB            |                 |      |      |       |          |                                 |
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| Examiner        | T. NGUYEN |   |
| Date Considered | 7/28/03   |   |

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